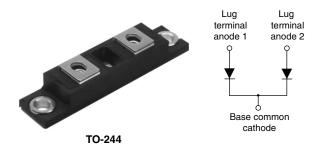


Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 320 A



PRODUCT SUMMARY				
I _{F(AV)}	320 A			
V _R	400 V			
I _{F(DC)} at T _C	255 A at 85 °C			

FEATURES

- Very low Q_{rr} and t_{rr}
- · Lead (Pb)-free
- · Designed and qualified for industrial level



ROHS

BENEFITS

- · Reduced RFI and EMI
- · Reduced snubbing

DESCRIPTION

HEXFRED[®] diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dI/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V_{R}		400	V	
		T _C = 25 °C	420		
Continuous forward current	I _F	T _C = 85 °C	255	Α	
		T _C = 115 °C	160		
Single pulse forward current	I _{FSM}	Limited by junction temperature	1200		
Non-repetitive avalanche energy	E _{AS}	$L = 100 \mu H$, duty cycle limited by maximum T_J	1.4	mJ	
Maximum power dissipation P _D		T _C = 25 °C	625	W	
		T _C = 100 °C	250	VV	
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to 150	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		400	-	-	
	I _F = 160 A		-	1.10	1.35	V	
Maximum forward voltage	V_{FM}	I _F = 320 A	See fig. 1	-	1.30	1.54	
		I _F = 160 A, T _J = 125 °C		-	1.00	1.20	
Maximum reverse leakage current	I _{RM}	T _J = 125 °C, V _R = 400 V See fig. 2		-	0.9	3	mA
Junction capacitance	C _T	V _R = 200 V See fig. 3		-	370	500	pF
Series inductance	L _S	From top of terminal hole to mounting plane		-	5.0	-	nH

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ - $T_J = 25 \text{ °C}$ - $T_J = 125 \text{ °C}$ -	I _F = 1.0 A, dI _F /dt = 200 A/μs.		-	45 -			
Reverse recovery time See fig. 5		T _J = 25 °C		=	90	140	ns	
occ fig. 5		T _J = 125 °C		=	290	440		
Peak recovery current	I _{RRM} -	T _J = 25 °C		-	8.7	20	^	
See fig. 6		IRRM	T _J = 125 °C	$I_F = 160 \text{ A}$	-	18	30	Α
Reverse recovery charge	Q _{rr}	T _J = 25 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	=	420	1100	nC	
See fig. 7		T _J = 125 °C		=	2600	7000	IIC IIC	
Peak rate of recovery current	Peak rate of recovery current	-II /-II	T _J = 25 °C		=	300	-	Δ/110
See fig. 8 dI _{(rec)M} /dt	T _J = 125 °C		=	280	-	A/μs		

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature	range	T _J , T _{Stg}	- 55	-	150	°C	
Thermal registence, junction to acce	per leg	D	-	-	0.19	°C/W K/W	
Thermal resistance, junction to case -	per module	R_{thJC}	-	-	0.095		
Typical thermal resistance, case to heatsink		R _{thCS}	-	0.10	-	17/ 77	
Woight			-	68	-	g	
Weight			-	2.4	-	OZ.	
Mounting towns	(1)		30 (3.4)	-	40 (4.6)	NI	
Mounting torque	center hole		12 (1.4)	-	18 (2.1)	N ⋅ m (lbf ⋅ in)	
Terminal torque			30 (3.4)	-	40 (4.6)	(151 * 111)	
Vertical pull 2" lever pull			-	-	80	11.6	
			-	-	35	lbf ⋅ in	

Note

⁽¹⁾ Mounting surface must be smooth, flat, free of burrs or other protrusions. Apply a thin even film or thermal grease to mounting surface. Gradually tighten each mounting bolt in 5 to 10 lbf · in steps until desired or maximum torque limits are reached.





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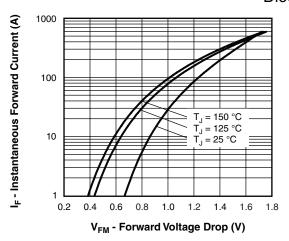


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

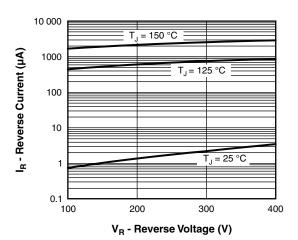


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

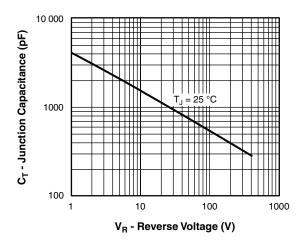


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

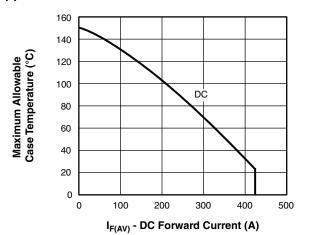


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current (Per Leg)

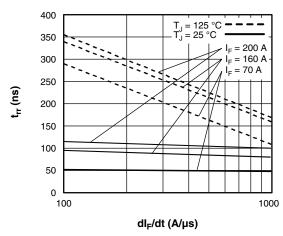


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

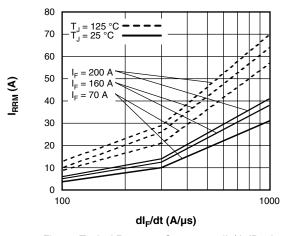


Fig. 6 - Typical Recovery Current vs. dI_F/dt (Per Leg)

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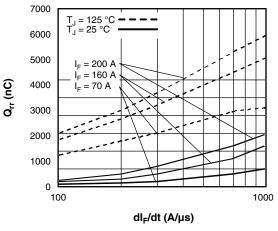


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

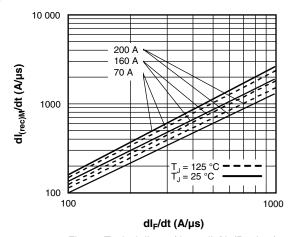


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)

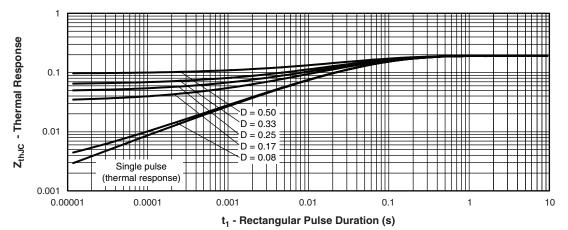


Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)



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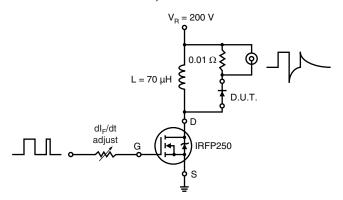
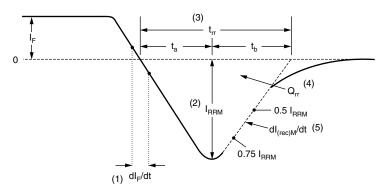


Fig. 10 - Reverse Recovery Parameter Test Circuit



- dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

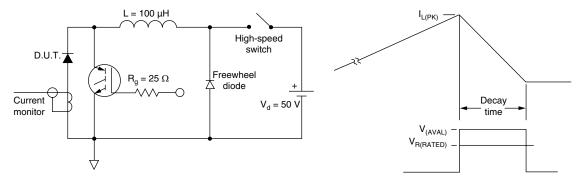


Fig. 12 - Avalanche Test Circuit and Waveforms

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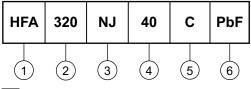
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ORDERING INFORMATION TABLE

Device code



1 - HEXFRED® family, electron irradiated

Average current rating

3 - NJ = TO-244

4 - Voltage rating (400 V)

5 - C = Common cathode

6 - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions	http://www.vishay.com/doc?95021			



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